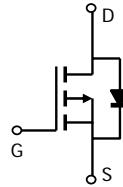
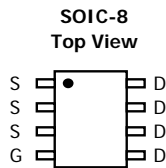



**AO4459**
**P-Channel Enhancement Mode Field Effect Transistor**
**General Description**

The AO4459 uses advanced trench technology to provide excellent  $R_{DS(ON)}$  with low gate charge. This device is suitable for use as a load switch or in PWM applications. *Standard product AO4459 is Pb-free (meets ROHS & Sony 259 specifications). AO4459L is a Green Product ordering option. AO4459 and AO4459L are electrically identical.*

**Features**

$V_{DS} (V) = -30V$   
 $I_D = -6.5A \quad (V_{GS} = -10V)$   
 $R_{DS(ON)} < 46m\Omega \quad (V_{GS} = -10V)$   
 $R_{DS(ON)} < 72m\Omega \quad (V_{GS} = -4.5V)$


**Absolute Maximum Ratings  $T_A=25^\circ C$  unless otherwise noted**

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	$V_{DS}$	-30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current <sup>A</sup>	$I_D$	$T_A=25^\circ C$	-6.5
		$T_A=70^\circ C$	-5.3
Pulsed Drain Current <sup>B</sup>	$I_{DM}$	-30	A
Power Dissipation <sup>A</sup>	$P_D$	$T_A=25^\circ C$	3.1
		$T_A=70^\circ C$	2
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	$^\circ C$

**Thermal Characteristics**

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient <sup>A</sup>	$R_{\theta JA}$	33	40	$^\circ C/W$
$t \leq 10s$				
Maximum Junction-to-Ambient <sup>A</sup>	$R_{\theta JA}$	62	75	$^\circ C/W$
Steady-State				
Maximum Junction-to-Lead <sup>C</sup>	$R_{\theta JL}$	18	24	$^\circ C/W$

Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	I <sub>D</sub> =-250μA, V <sub>GS</sub> =0V	-30			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =-24V, V <sub>GS</sub> =0V T <sub>J</sub> =55°C			-1 -5	μA
I <sub>GSS</sub>	Gate-Body leakage current	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V			±100	nA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250μA	-1.5	-1.85	-2.5	V
I <sub>D(ON)</sub>	On state drain current	V <sub>GS</sub> =-10V, V <sub>DS</sub> =-5V	-30			A
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =-10V, I <sub>D</sub> =-6.5A T <sub>J</sub> =125°C		38 53	46 68	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-5A		58	72	
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> =-5V, I <sub>D</sub> =-6.5A		11		S
V <sub>SD</sub>	Diode Forward Voltage	I <sub>S</sub> =-1A, V <sub>GS</sub> =0V		-0.78	-1	V
I <sub>S</sub>	Maximum Body-Diode Continuous Current				-3.5	A
<b>DYNAMIC PARAMETERS</b>						
C <sub>ISS</sub>	Input Capacitance	V <sub>GS</sub> =0V, V <sub>DS</sub> =-15V, f=1MHz		668	830	pF
C <sub>OSS</sub>	Output Capacitance			126		pF
C <sub>RSS</sub>	Reverse Transfer Capacitance			92		pF
R <sub>g</sub>	Gate resistance	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1MHz		6	9	Ω
<b>SWITCHING PARAMETERS</b>						
Q <sub>g</sub> (10V)	Total Gate Charge (10V)	V <sub>GS</sub> =-10V, V <sub>DS</sub> =-15V, I <sub>D</sub> =-6.5A		12.7	16	nC
Q <sub>g</sub> (4.5V)	Total Gate Charge (4.5V)			6.4		nC
Q <sub>gs</sub>	Gate Source Charge			2		nC
Q <sub>gd</sub>	Gate Drain Charge			4		nC
t <sub>D(on)</sub>	Turn-On DelayTime	V <sub>GS</sub> =-10V, V <sub>DS</sub> =-15V, R <sub>L</sub> =2.5Ω, R <sub>GEN</sub> =3Ω		7.7		ns
t <sub>r</sub>	Turn-On Rise Time			6.8		ns
t <sub>D(off)</sub>	Turn-Off DelayTime			20		ns
t <sub>f</sub>	Turn-Off Fall Time			10		ns
t <sub>rr</sub>	Body Diode Reverse Recovery Time		I <sub>F</sub> =-6.5A, di/dt=100A/μs		22	30
Q <sub>rr</sub>	Body Diode Reverse Recovery Charge	I <sub>F</sub> =-6.5A, di/dt=100A/μs		15		nC

A: The value of R<sub>θJA</sub> is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25°C. The value in any a given application depends on the user's specific board design. The current rating is based on the t ≤ 10s thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C. The R<sub>θJA</sub> is the sum of the thermal impedance from junction to lead R<sub>θJL</sub> and lead to ambient.

D. The static characteristics in Figures 1 to 6 are obtained using < 300μs pulses, duty cycle 0.5% max.

E. These tests are performed with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25°C. The SOA curve provides a single pulse rating.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

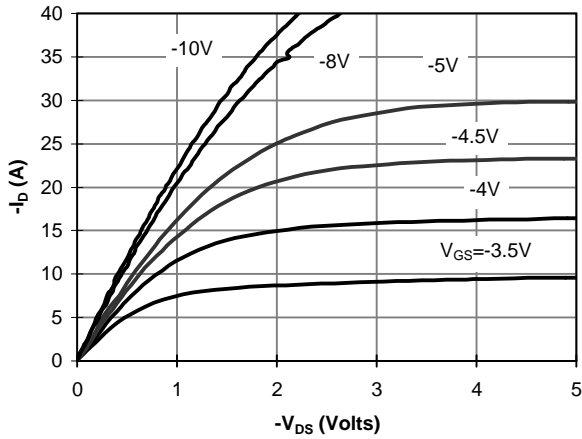


Figure 1: On-Region Characteristics

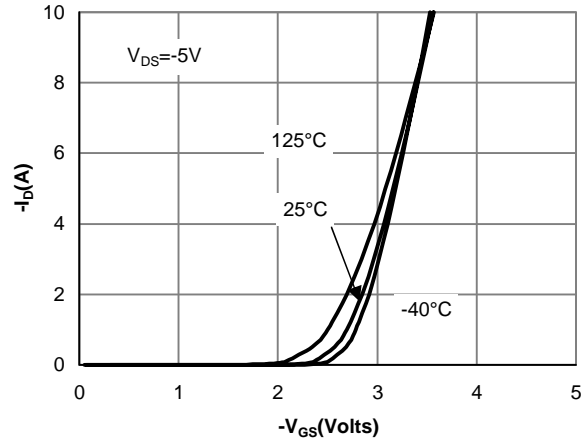


Figure 2: Transfer Characteristics

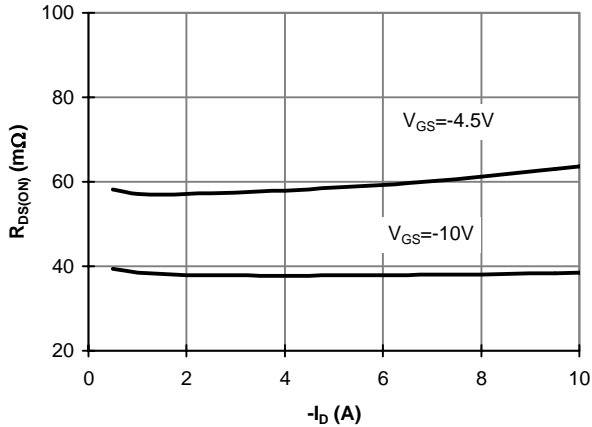


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

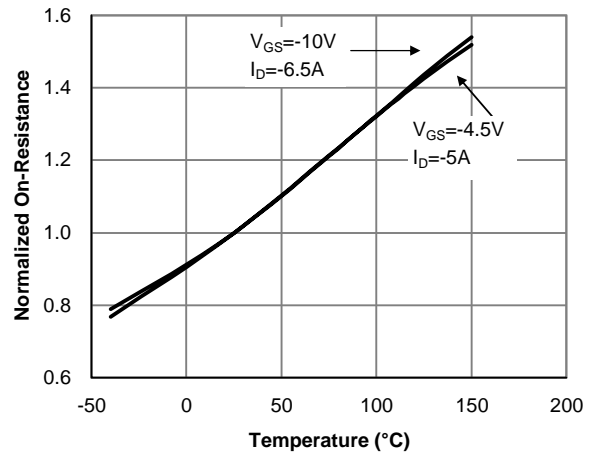


Figure 4: On-Resistance vs. Junction Temperature

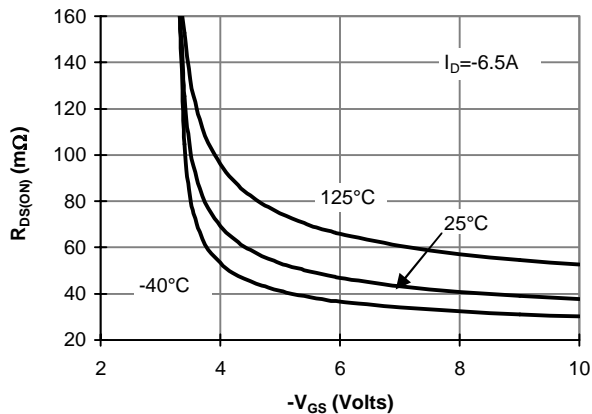


Figure 5: On-Resistance vs. Gate-Source Voltage

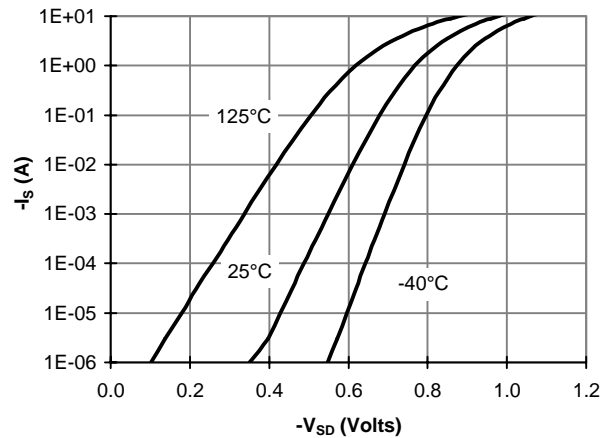


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

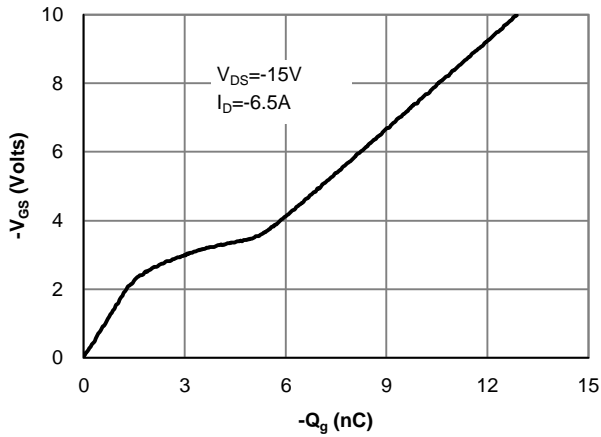


Figure 7: Gate-Charge Characteristics

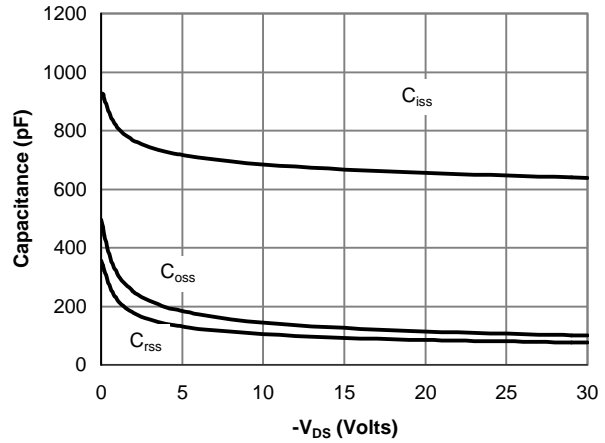


Figure 8: Capacitance Characteristics

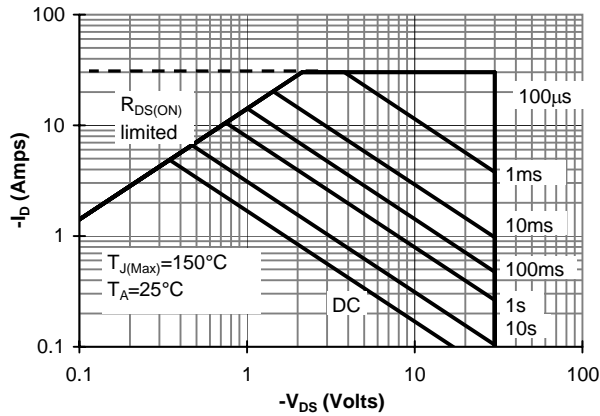


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

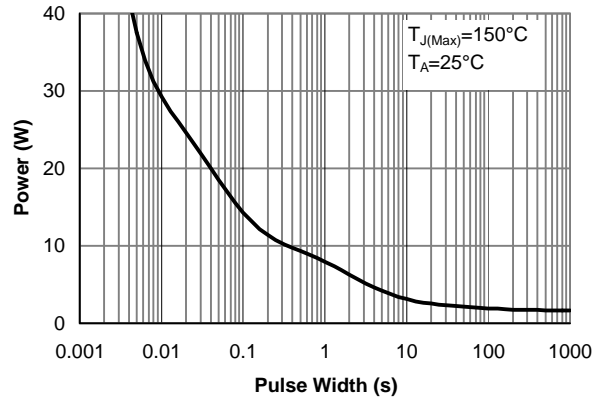


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

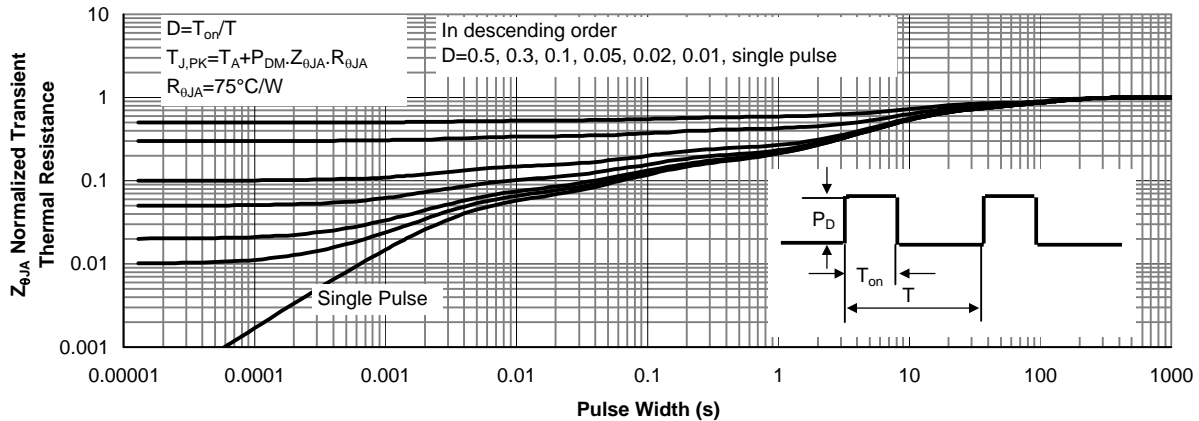


Figure 11: Normalized Maximum Transient Thermal Impedance (Note E)